

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known		
				Application Number	10/802,186-Conf. #3869	
				Filing Date	March 17, 2004	
				First Named Inventor	Cheng	
				Art Unit	2811	
Examiner Name	Shouxiang Hu					
Attorney Docket Number	ASC-025DV2C1					
Sheet	1	of	3			

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	B51	JP-3-036717	02-18-1991			✓
	B52	JP-6-244112	09-02-1994		Abstract only	✓
	B53	JP-6-252046	09-09-1994		Abstract only	✓
	B54	JP-61-141116	06-28-1986		Abstract only	✓

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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C170	Examination Report for European Patent Application No. 01 973 651.1-1528, dated November 12, 2004, 9 pages.	
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C172	Examination Report for European Patent Application No. 02 709 406.9-2203, dated March 24, 2005, 5 pages.	
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